DP8205C

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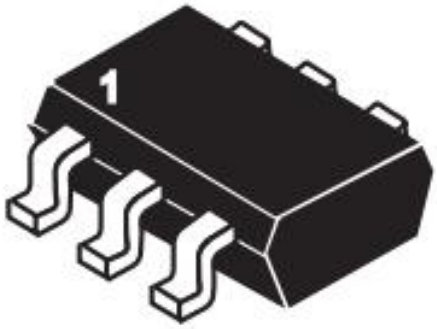
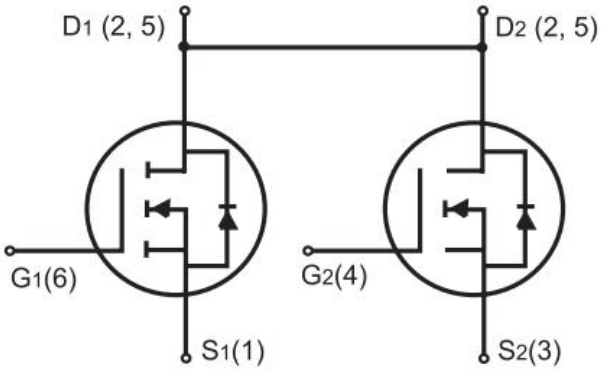
Dual N-Channel Enhancement Power MOSFET

Rev1.0

General Description	Product Summary	
DP8205 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.	V_{DS}	16 V
	I_D (at V_{GS}=4.5V)	5.0A
	$R_{DS(ON)}$ (at V_{GS} = 4.5V)	< 29mΩ
	$R_{DS(ON)}$ (at V_{GS} = 2.5V)	< 34mΩ

SOT23-6





Absolute Maximum Ratings TA=25°C unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	16	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous @ T_J=25℃	I_D	5	A
Pulsed[b]	I_{DM}	20	A
Drain-Sourse Diode Forward Current[a]	I_S	2.5	A
Maximum Power Dissipation[a]	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Parameter	Symbol	Limit	Unit
Thermal Resistance,Junction-to-Ambient [a]	$R_{\theta JA}$	100	℃/W